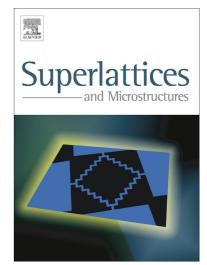
### Accepted Manuscript

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## **ACCEPTED MANUSCRIPT**

# Electrochemical growth of GaSe nanostructures and their Schottky barrier characteristics

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#### Highlights

- Highly crystalline GaSe thin film was synthesized by electrochemical deposition.
- It has a hexagonal structure with preferential orientation along (004) plane.
- EDS showed that the prepared film has high purity.
- The barrier height of the diode is temperature dependent.
- This diode can be used as efficient temperature sensor.

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